

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 192520US2		SERIAL NO. <u>09/594,479</u> <del>New Application</del>	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Hayashi OTSUKI, et al.			
				FILING DATE <u>6/14/2000</u> <small>Herewith</small>		GROUP <u>2877</u>	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	5,271,264	12/21/93	Steve G. Chanayem	—	—	
	AB	5,347,138	09/13/94	Derek G. Aqui, et al.	—	—	
	AC	5,438,526	08/01/95	Satoshi Itoh, et al.	—	—	
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO	6-110870	04/22/94	Japan (with English Abstract)			x
	AP	10-242060	09/11/98	Japan (with English Abstract)			x
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
	AW	Tom WINTER, et al., "ISPM CHARACTERIZATION OF GAS PHASE NUCLEATION IN A NOVELLUS C1 WCVD PROCESS CHAMBER," IEEE/SEMI Advanced Semiconductor Manufacturing Conference, 1995, pgs. 17-22					
	AX	Jenny ASBELL, et al., "IMPROVING TUNGSTEN CVD PERFORMANCE WITH IN SITU PARTICLE MONITORING," Micro, July/August 1997, pgs. 63-73					
	AY						
	AZ						
Examiner					Date Considered <u>SEP. 30, 2001</u>		

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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